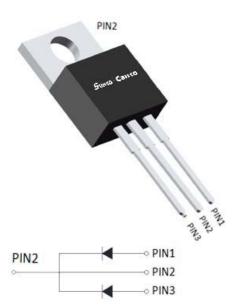


Schottky Diodes



Features

- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Solder dip 275 °C max. 7 s, per JESD 22-B106

Typical Applications

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

Mechanical Data

Package: TO-220AB

Molding compound meets III

Molding compound meets UL 94 V-0 flammability rating -

 Terminals: Tin plated leads, solderable per J-STD-002 and JESD22-B102

Polarity: As marked

■Maximum Ratings (Ta=25°C Unless otherwise specified)

= maximum (atmgs (1a 25 c cmost emermics opening)					
PARAMETER	SYMBOL	UNIT	MBR2045CTS		
Device marking code			MBR2045CTS		
Repetitive Peak Reverse Voltage	VRRM	V	45		
Average Rectified Output Current @60Hz sine wave, R-load, Ta=25℃	IO	Α	20		
Surge(Non-repetitive)Forward Current @60H _Z half sine-wave,1 cycle, T _a =25℃	IFSM	Α	130		
Current Squared Time @1ms≤t<8.3ms Tj=25℃,	l²t	A ² s	70		
Storage Temperature	T _{stg}	°C	-55 ~ + 150		
Junction Temperature	Tj	$^{\circ}$	-55 ~ + 150		

■Electrical Characteristics (T_a=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBR2045CTS
Maximum instantaneous forward voltage drop per diode	VFM	٧	IFM=10.0A	0.65
Maximum DC reverse current at rated DC blocking voltage per- diode	IRRM1	mA -	VRM=VRRM T _a =25°C	0.2
	IRRM2		VRM=VRRM T _a =125°C	100

Note1:Pulse test:300uS pulse widh,1% duty cycle

Note2:Pulse test:pulse widh 40mS



■Thermal Characteristics (T_a=25°C Unless otherwise specified)

PARAMETER		SYMBOL	UNIT	MBR2045CTS
Thermal Resistance	Between junction and case	R _{θJ-С}	°C W	2.0

■Ordering Information (Example)

PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MBR2045CTS	Approximate 1.9	50	1000	5000	Tube

■Characteristics (Typical)

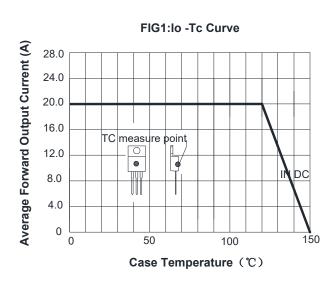
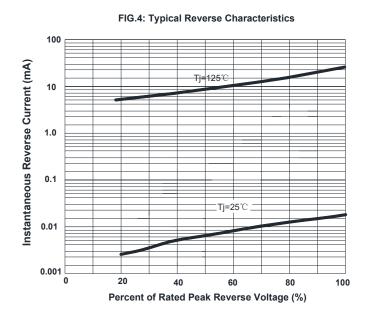


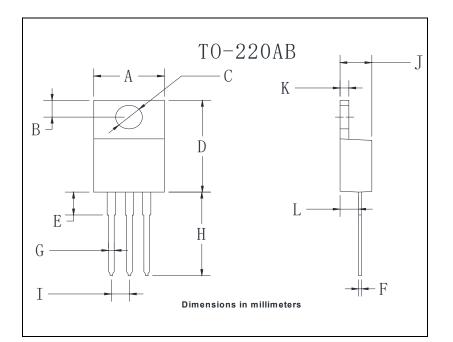
FIG2:Surge Forward Current Capability 170 Peak Forward Surge Current (A) 150 130 8.3ms Single Half Sine-Wave 110 JEDEC Method 90 70 50 2 20 5 10 50 100 **Number of Cycles**

FIG3: Forward Voltage 100 60 Instantaneous Forward Current (A) 20 10 5.0 1.0 0.5 0.2 Ta=25℃ 0.5 0.6 0.7 8.0 1.0 Instantaneous Forward Voltage (V)





■Outline Dimensions



TO-220AB					
Dim	Min	Max			
Α	9.95	10.35			
В	2.55	2.95			
С	3.8	4.0			
D	14.95	15.25			
E	3.75	4.25			
F	0.26	0.5			
G	0.68	0.94			
Н	13.4	13.9			
I	2.35	2.65			
J	4.38	4.78			
K	1.14	1.4			
L	2.37	2.79			



Disclaimer

The information presented in this document is for reference only. Shanghai Sunco Electronics Co., Ltd reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Russiansunco or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website http:// www.russiansunco.com , or consult your nearest Russiansunco's sales office for further assistance.